



6102  
#10/C 3/ attachments  
OK  
2/21/03  
PATENT  
8095DIV4  
JAN-2 2003  
RECEIVED  
TECHNOLOGY CENTER 2800

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Art Unit: 2815

Examiner: Richards

In re application of  
Gonzalez et al.

Serial No.: 10/008,653

Filed: November 9, 2001

SEMICONDUCTOR RAISED  
SOURCE-DRAIN STRUCTURE

AMENDMENT AND RESPONSE TO OFFICE ACTION

December 24, 2002

Commissioner for Patents  
Washington, D.C. 20231

Dear Commissioner:

In response to the office action dated October 2, 2002 with respect to the above-identified application ("subject application"), please amend the subject application as follows:

Please cancel claims 29, 30, 104-112, 114-117, 119, 120, 122, and 123, without prejudice or disclaimer to the subject matter contained therein.

Please amend the claims as follows:

- C1  
Con't  
mud
17. (Twice Amended) A transistor formed on a substrate assembly, comprising:  
a raised drain structure;  
a raised source structure;  
a gate located between said source and said drain;

12/30/2002 MDAMTE1 00000039 10008653

01 FC:1252

400.00 OP